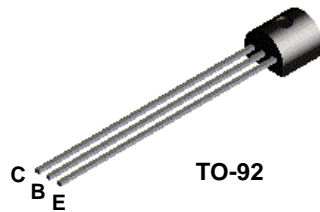
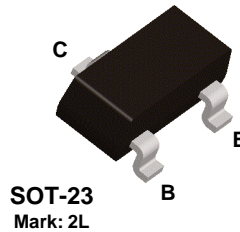


2N5401



MMBT5401



PNP General Purpose Amplifier

This device is designed as a general purpose amplifier and switch for applications requiring high voltages. Sourced from Process 74.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	150	V
V _{CBO}	Collector-Base Voltage	160	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5401	*MMBT5401	
P _D	Total Device Dissipation Derate above 25°C	625	350	mW
		5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	150		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	160		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 120 \text{ V}, I_E = 0$ $V_{CB} = 120 \text{ V}, I_E = 0, T_A = 100^\circ\text{C}$		50 50	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		50	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$	50 60 50	240	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2 0.5	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		1.0 1.0	V V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	100	300	MHz
C_{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 1.0 \text{ MHz}$		6.0	pF
NF	Noise Figure	$I_C = 250 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega,$ $f = 10 \text{ Hz to } 15.7 \text{ kHz}$		8.0	dB

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

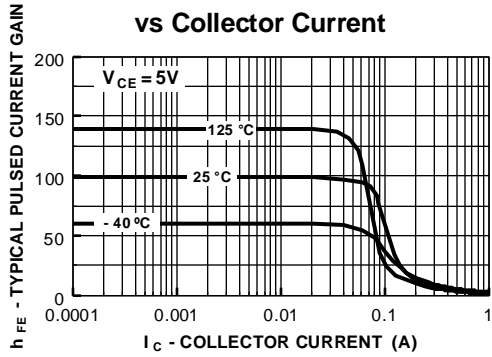
Spice Model

PNP (Is=21.48f Xti=3 Eg=1.11 Vaf=100 Bf=132.1 Ne=1.375 Ise=21.48f Ikf=.1848 Xtb=1.5 Br=3.661 Nc=2 Isc=0 Ikr=0 Rc=1.6 Cjc=17.63p Mjc=.5312 Vjc=.75 Fc=.5 Cje=73.39p Mje=.3777 Vje=.75 Tr=1.476n Tf=641.9p ltf=0 Vtf=0 Xtf=0 Rb=10)

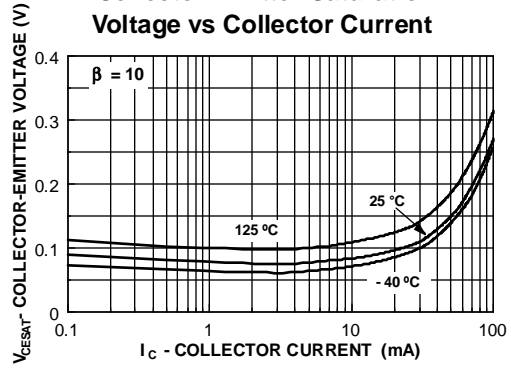
2N5401 / MMBT5401

Typical Characteristics

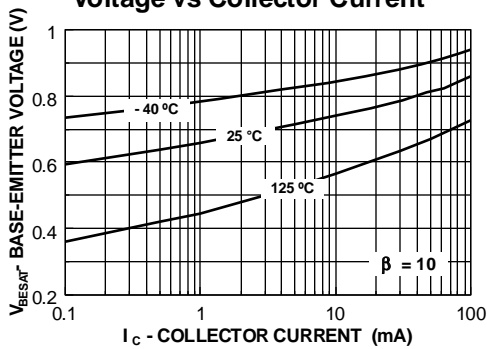
Typical Pulsed Current Gain vs Collector Current



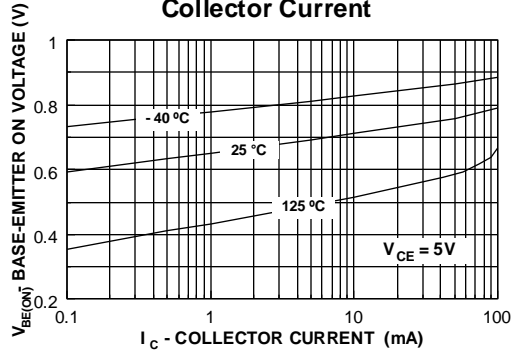
Collector-Emitter Saturation Voltage vs Collector Current



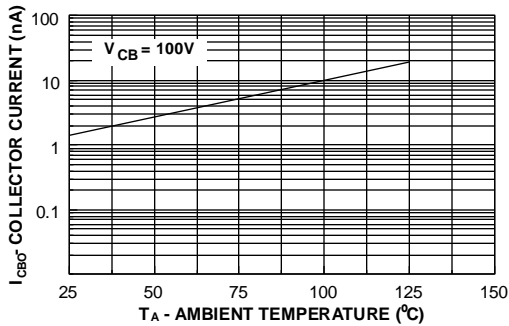
Base-Emitter Saturation Voltage vs Collector Current



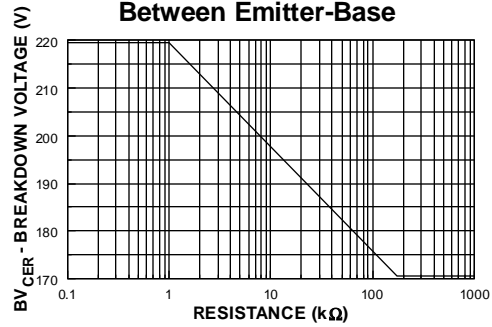
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

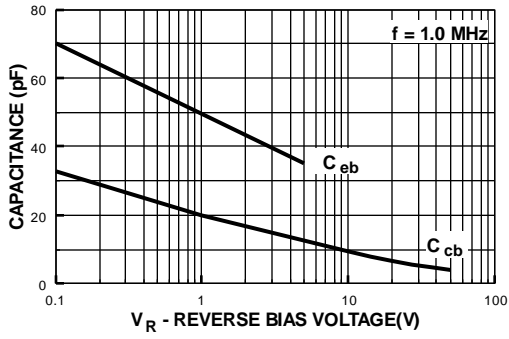


Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Typical Characteristics (continued)

Input and Output Capacitance vs Reverse Voltage



Power Dissipation vs Ambient Temperature

